2.5V drive

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K116TU

High Speed Switching Applications

• Low on-resistance: $R_{on} = 135m\Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$

 $R_{on} = 100 m\Omega \text{ (max) (@V_{GS} = 4.5 V)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Drain-Source voltage		V _{DS}	30	V	
Gate-Source voltage		V _{GSS}	± 12	V	
Drain current	DC	I _D	2.2	А	
	Pulse	I _{DP}	4.4		
Drain power dissipation		P _{D (Note 1)}	800	mW	
		P _{D (Note 2)}	500		
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	−55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure

rate, etc).

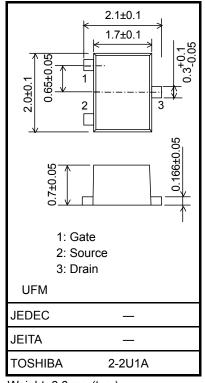
Note 1: Mounted on ceramic board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 0.8 \text{ mm}, \text{ Cu Pad: } 645 \text{ mm}^2)$

Note 2: Mounted on FR4 board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ mm}, \text{ Cu Pad: } 645 \text{ mm}^2)$

Unit: mm



Weight: 6.6 mg (typ.)

Electrical Characteristics (Ta = 25°C)

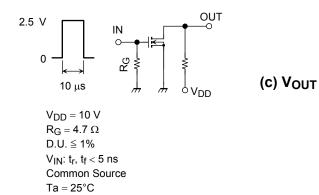
Charact	eristic	Symbol	Test Conditions	Min	Тур.	Max	Unit	
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	30	_	_	V	
		V (BR) DSX	$I_D = 1 \text{ mA}, V_{GS} = -12 \text{ V}$	18	_		V	
Drain cut-off curren	t	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0$	_	_	1	μА	
Gate leakage curre	nt	I _{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$	_	_	±1	μА	
Gate threshold volta	age	V _{th}	V _{DS} = 3 V, I _D = 0.1 mA	0.5	_	1.1	V	
Forward transfer ac	Imittance	Y _{fs}	$V_{DS} = 3 \text{ V}, I_D = 0.25 \text{ A}$ (Note3)	1	2		S	
Drain-Source on-resistance		R _{DS} (ON)	$I_D = 0.5 \text{ A}, V_{GS} = 4.5 \text{ V}$ (Note3)	_	75	100	mΩ	
			$I_D = 0.25 \text{ A}, V_{GS} = 2.5 \text{ V}$ (Note3)	_	95	135		
Input capacitance		C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	245		pF	
Output capacitance	apacitance C_{OSS} $V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		_	41	_	pF		
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	33	_	pF	
Switching time	Turn-on time	t _{on}	$V_{DD} = 10 \text{ V}, I_D = 0.25 \text{ A},$ $V_{GS} = 0 \sim 2.5 \text{ V}, R_G = 4.7 \Omega$	_	9	_	ns	
	Turn-off time	t _{off}		_	15	_		
Drain-Source forward voltage		V _{DSF}	$I_D = -2.2A, V_{GS} = 0 V$ (Note3)	_	-0.83	-1.2	V	

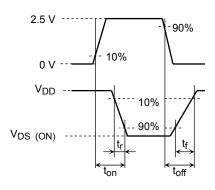
Note3: Pulse test

Switching Time Test Circuit

(a) Test Circuit

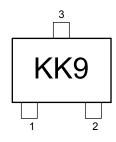
(b) V_{IN}

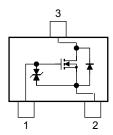




Marking

Equivalent Circuit (top view)





Precaution

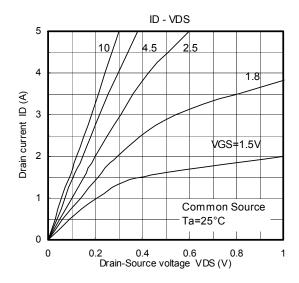
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is I_D =0.1mA for this product. For normal switching operation, V_{GS} (on) requires a higher voltage than V_{th} , and V_{GS} (off) requires a lower voltage than V_{th} .

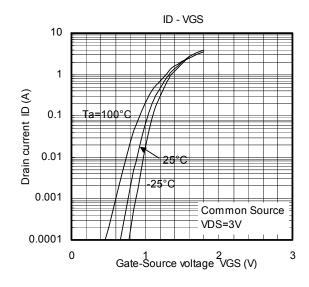
(The relationship can be established as follows: V_{GS} (off) < V_{th} < V_{GS} (on))

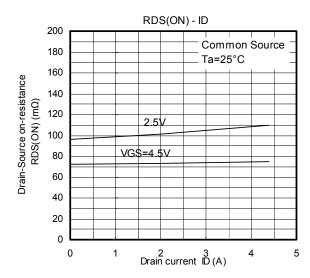
Take this into consideration when using the device.

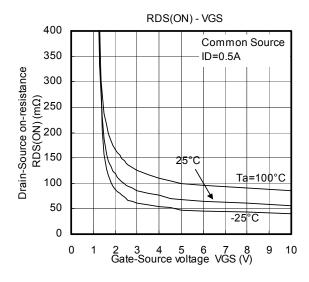
Handling Precaution

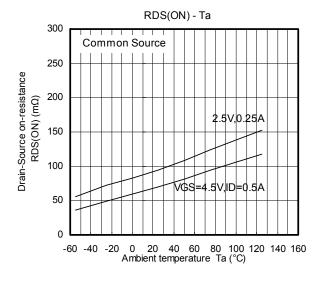
When handling individual devices which are not yet mounted on a circuit board, be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

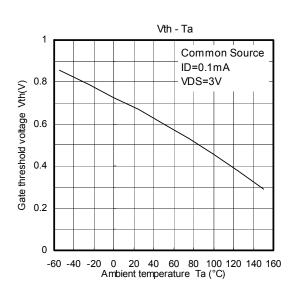




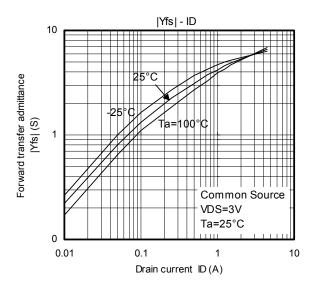


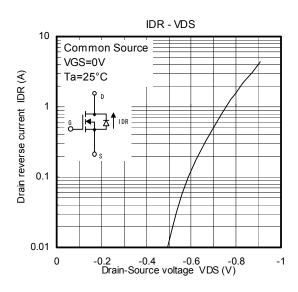


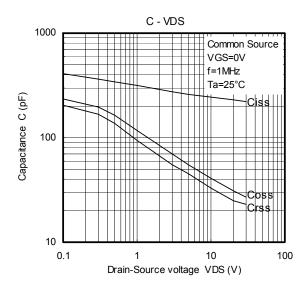


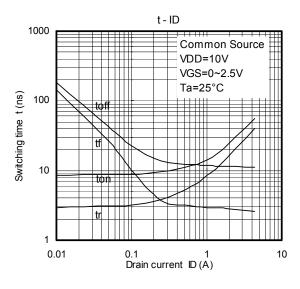


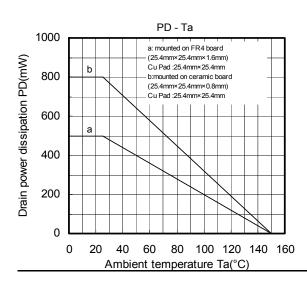
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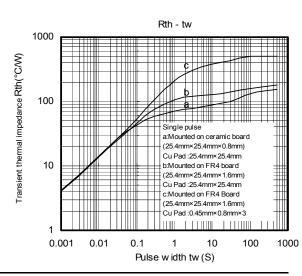












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20070701-EN GENERAL

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